

CMOS Digital Integrated Circuits Silicon Monolithic

Features

High speed: tpd = 15 ns (typ.) at $V_{CC} = 5 \text{ V}$

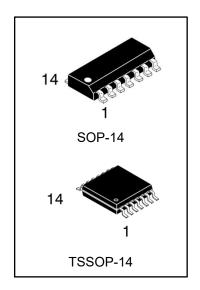
Low power dissipation: $I_{CC} = 4.0 \mu A \text{ (max)}$ at Ta = 25

Balanced propagation delays: t_{PLH} ≈ t_{PHL}

Wide operating voltage range: $V_{CC(opr)} = 2.0$ to 6.0 V

Functional Description

8-Channel Multiplexer



Ordering Information

DEVICE	Package Type	MARKING	Packing	Packing Qty
74HC151DRG	SOP-14	74HC151	REEL	2500pcs/reel
74HC151PWRG	TSSOP-14	HC151	REEL	2500pcs/reel

Genearl Description

The 74HC151 is a high speed CMOS 8-CHANNEL MULTIPLEXER fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

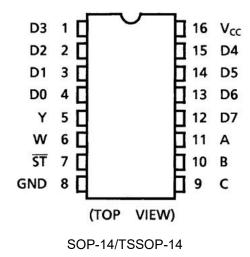
One of eight date input signals (D0-D7) is selected by decoding of the three-bit address input (A, B, C). The selected data appears on two outputs: non-inverting (Y) and inverting (W).

The strobe input provides two output conditions; a low level on the strobe input transfers the selected data to the outputs. A high level on the strobe input sets the Y output low and the W output high without regard to the data or select input conditions.

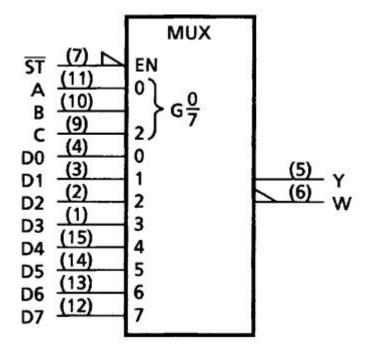
All inputs are equipped with protection circuits against static discharge or transient excess voltage.



Pin Assignment



IEC Logic Symbol



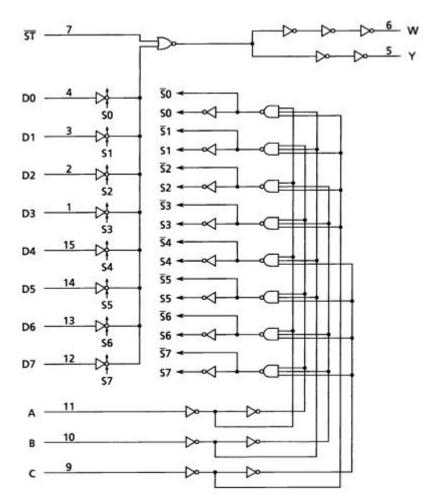


Truth Table

	Inp		Outputs		
	Select		Strobe	Y	14/
С	В	Α	ST	ľ	W
X	X	X	Н	L	Н
L	L	L	L	D0	⊡0
L	L	Н	L	D1	D 1
L	Н	L	L	D2	Ū2
L	Н	Н	L	D3	D 3
Н	L	L	L	D4	-
Н	L	Н	L	D5	D̄5
Н	Н	L	L	D6	Ō6
Н	Н	Н	L	D7	Ū7

X:Don`t care

System Diagram





Absolute Maximum Ratings (Note)

Characteristics	Symbol	Note	Rating	Unit
Supply voltage	Vcc		-0.5 to 7.0	V
Input voltage	Vin		-0.5 to V _{CC} + 0.5	V
Output voltage	V _{OUT}		-0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}		20	mA
Output diode current	Іок		20	mA
Output current	I _{OUT}		25	mA
VCC/ground current	Icc		50	mA
Power dissipation	P _D	(Note 1)	500	mW
Storage temperature	Tstg		-65 to 150	°C
Soldering temperature	T∟		245	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Note 1: PD derates linearly with -8 mW/ above 85

Operating Ranges (Note)

Characteristics	Symbol	Test Condition	Rating	Unit
Supply voltage	Vcc		2.0 to 6.0	V
Input voltage	Vin		0 to VCC	V
Output voltage	V _{OUT}		0 to VCC	V
Operating temperature	Topr		-40 to 85	°C
Input rise and fall times	tr,tf		0 to 50	μs

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.



Electrical Characteristics

DC Characteristics (Unless otherwise specified, Ta = 25°C)

Characteristics	Symbol	Test Con	dition	Vcc (V)	Min	Тур.	Max	Unit
				2.0	1.50			
High-level input voltage	V _{IH}			4.5	3.15			V
				6.0	4.20			
							0.50	
Low-level input voltage	VIL			4.5			1.35	V
			6.0			1.80		
	V _{ОН}	V _{IN} = V _{IH} or V _{IL}		2.0	1.9	2.0		
			I _{OH} = -20μA	4.5	4.4	4.5		
High-level output voltage				6.0	5.9	6.0		V
			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31		
			I _{OH} =-5.2 mA	6.0	5.68	5.80		
				2.0		0.0	0.1	
			I _{OL} =20µA	4.5		0.0	0.1]
Low-level output voltage	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}		6.0		0.0	0.1	V
			I _{OL} =4 mA	4.5		0.17	0.26	
			I _{OL} =5.2 mA	6.0		0.18	0.26	
Input leakage current	I _{IN}	$V_{IN} = V_{CC} c$	V _{IN} = V _{CC} or GND				±0.1	μA
Quiescent supply current	Icc	$V_{IN} = V_{CC} c$	or GND	6.0			4.0	μA

DC Characteristics (Unless otherwise specified, Ta = -40 to 85°C)

Characteristics	Symbol	Test Con	dition	Vcc (V)	Min	Max	Unit
				2.0	1.50		
High-level input voltage	VIH			4.5	3.15		V
				6.0	4.20		
				2.0		0.50	
Low-level input voltage	VIL					1.35	V
				6.0		1.80	
High-level output voltage	Vон	$V_{IN} = V_{IH}$ or V_{IL}		2.0	1.9		
			I _{OH} = -20μA	4.5	4.4		
				6.0	5.9		V
			I _{OH} = -4 mA	4.5	4.13		
			I _{OH} =-5.2 mA	6.0	5.63		
				2.0		0.1	
			I _{OL} =20µA	4.5		0.1	V
Low-level output voltage	V _{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$		6.0		0.1	
			I _{OL} =4 mA	4.5		0.33	
			I _{OL} =5.2 mA	6.0		0.33	
Input leakage current	I _{IN}	$V_{IN} = V_{CC}$	or GND	6.0		±1.0	μA
Quiescent supply current	Icc	$V_{IN} = V_{CC}$	or GND	6.0		40.0	μA



AC Characteristics

(Unless otherwise specified, C_L = 15 pF, V_{CC} = 5 V, Ta = 25°C, Input: tr = tf = 6 ns)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Output transition time	t _{TLH} ,t _{THL}			4	8	ns
Propagation delay time (D-Y)	t _{PLH} ,t _{PHL}			15	24	ns
Propagation delay time (D-W)	t _{PLH} ,t _{PHL}			15	24	ns
Propagation delay time (ST-Y)	t _{РСН} ,t _{РНС}			10	17	ns
Propagation delay time (ST-W)	t _{PLH} ,t _{PHL}			10	17	ns
Propagation delay time (A, B, C-Y)	t _{PLH} ,t _{PHL}			19	31	ns
Propagation delay time (A, B, C-W)	t _{PLH} ,t _{PHL}			19	31	ns

AC Characteristics

(Unless otherwise specified, CL = 50 pF, Ta = 25°C, Input: tr = tf = 6 ns)

Characteristics	Symbol	Note	V _{cc} (V)	Min	Тур.	Max	Unit
			2.0		30	75	
Output transition time	t _{TLH} ,t _{THL}		4.5		8	15	ns
			6.0		7	13	
			2.0		65	140	
Propagation delay time (D-Y)	t _{PLH} ,t _{PHL}		4.5		18	28	ns
			6.0		15	24	
			2.0		65	140	
Propagation delay time (D-W)	t _{PLH} ,t _{PHL}		4.5		18	28	ns
			6.0		15	24	
			2.0		36	100	
Propagation delay time (ST-Y)	t _{PLH} ,t _{PHL}		4.5		12	20	ns
			6.0		10	17	<u> </u>
			2.0		36	100	
Propagation delay time (ST-W)	t _{PLH} ,t _{PHL}		4.5		12	20	ns
			6.0		10	17	
			2.0		80	180	
Propagation delay time (A, B, C-Y)	t _{PLH} ,t _{PHL}		4.5		23	36	ns
			6.0		19	31	
			2.0		80	180	
Propagation delay time (A, B, C-W)	t _{PLH} ,t _{PHL}		4.5		23	36	ns
			6.0		19	31	
Input capacitance	C _{IN}				3		pF
Power dissipation capacitance	C _{PD}	(Note 1)			15		pF

Note 1: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation.

 $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$



AC Characteristics

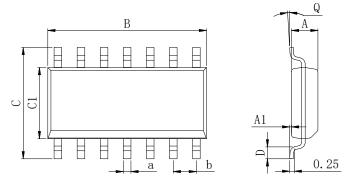
(Unless otherwise specified, C_L = 50 pF, T_a = -40 to 85°C, Input: t_r = t_f = 6 ns)

Characteristics	Symbol	V _{cc} (V)	Min	Max	Unit
		2.0		95	
Output transition time	t _{TLH} ,t _{THL}	4.5		19	ns
		6.0		16	
		2.0		175	
Propagation delay time (D-Y)	t _{PLH} ,t _{PHL}	4.5		35	ns
		6.0		30	
		2.0		175	
Propagation delay time (D-W)	t _{PLH} ,t _{PHL}	4.5		35	ns
		6.0		30	
		2.0		125	ns
Propagation delay time (ST-Y)	t _{PLH} ,t _{PHL}	4.5		25	
		6.0		21	
		2.0		125	ns
Propagation delay time (ST-W)	t _{PLH} ,t _{PHL}	4.5		25	
		6.0		21	
		2.0		225	
Propagation delay time (A, B, C-Y)	t _{PLH} ,t _{PHL}	4.5		45	ns
		6.0		38	
		2.0		225	
Propagation delay time (A, B, C-W)	t _{PLH} ,t _{PHL}	4.5		45	ns
		6.0		38	



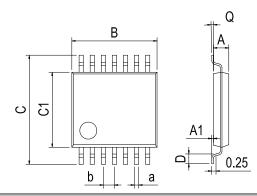
Physical Dimensions

SOP-14



Dimensions In Millimeters(SOP14)										
Symbol:	Α	A1	В	С	C1	D	Q	а	b	
Min:	1.35	0.05	8.55	5.80	3.80	0.40	0°	0.35	4.07.000	
Max:	1.55	0.20	8.75	6.20	4.00	0.80	8°	0.45	1.27 BSC	

TSSOP-14



Dimensions In Millimeters(TSSOP14)									
Symbol:	Α	A1	В	С	C1	D	Q	а	b
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	0.00 BSC

2014 JUN



Revision History

DATE	REVISION	PAGE
2014-6-8	New	1-10
2023-7-22	Update encapsulation type、Update Soldering temperature	1、4



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